

## ABSTRACT

A substrate for growth of nitride semiconductor capable of obtaining a high-quality nitride semiconductor crystal layer is provided. A substrate for growth of nitride semiconductor for growth of a nitride semiconductor layer on a sapphire substrate (1) according to one embodiment of the invention is provided with an  $\text{Al}_2\text{O}_3$  layer (2) as separately provided on the sapphire substrate (1), an AlON layer (3) which is the first layer, and an AlN layer (4) which is the second layer. With respect to the first layer and the second layer, the AlON layer (3) and the AlN layer (4) are deposited on the  $\text{Al}_2\text{O}_3$  layer (2) in this order.